



## KL2G-1010-SiO<sub>2</sub>/Si

KL2G-1010-SiO<sub>2</sub>/Si is a single 10mmx10mm bilayer of CVD graphene film, on silicon. Both layers of graphene were grown on copper foil, and transferred individually by wet film transfer to the silicon substrate.

### Graphene Film

Growth Method	CVD synthesis
Transfer Method	Clean transfer method
Quality Control	Optical Microscopy & Raman checked
Appearance (Color)	Transparent
Transparency	>97%
Appearance (Form)	Film
Coverage	>95%
Number of graphene layers	2
Thickness (theoretical)	0.345 nm
Field Effect Mobility on SiO <sub>2</sub> /Si	2,000 cm <sup>2</sup> /V·s
Hall Effect Mobility on SiO <sub>2</sub> /Si	4,000 cm <sup>2</sup> /V·s
Sheet Resistance on SiO <sub>2</sub> /Si (Van der Pauw)	190±30 Ohms/sq. (1cm x 1cm)
Grain size	Up to 10 μm

### Substrate

	<b>SiO<sub>2</sub>/Si</b>
Type/Dopant	P/Bor
Orientation	<100>
Growth Method	CZ
Resistivity	<0.005 ohm cm
Thickness	525 +/- 20 μm
Front Surface	Polished
Back Surface	Etched
Flats	2 SEMI

### Optical Microscopy

